

28x28mil Silicon PD Chip datasheet

P/N : WS59-10C

Application

The specification applies to NIP photodetectors.

Structure:

NIP planar type

Electrode:

Topside (cathode) : Aluminum

Backside (anode) : Au Alloy

Size:

Chip size	28mil × 28mil (± 1.5mil)
Thickness	12mil ± 0.4mil
Active area	22mil × 22mil (± 1.0mil)
Electrode size	6mil × 6mil
Pattern drawing	per fig. 1

Electro-Optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	VF	IF=10mA, H=0	0.5		1.2	V
Reverse Breakdown Voltage	VBR	IR=100μA, H=0	35			V
Reverse Dark Current	ID	VR=10V, H=0			10	nA
Capacitance	CJ	VR=3V, F=1 MHz		9		pF
Sensitive Wavelength Peak	λp		400	940	1100	nm

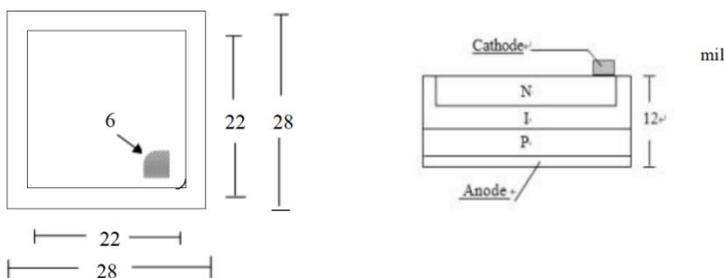


Fig.1